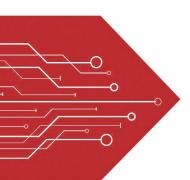
MSKSEMI















ESD

TVS

TSS

MOV

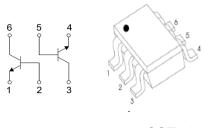
GDT

PLED

Brodnet data speet

www.msksemi.com





SOT-363

MMDT4401

DUAL TRANSISTOR (NPN+NPN)

FEATURES

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

MRKING:K2X

Maximum Ratings (Ta = 25℃ unless otherwise specified)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current -Continuous	0.6	Α
Pc	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature	-55 to +150	$^{\circ}$

NPN 4401 ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

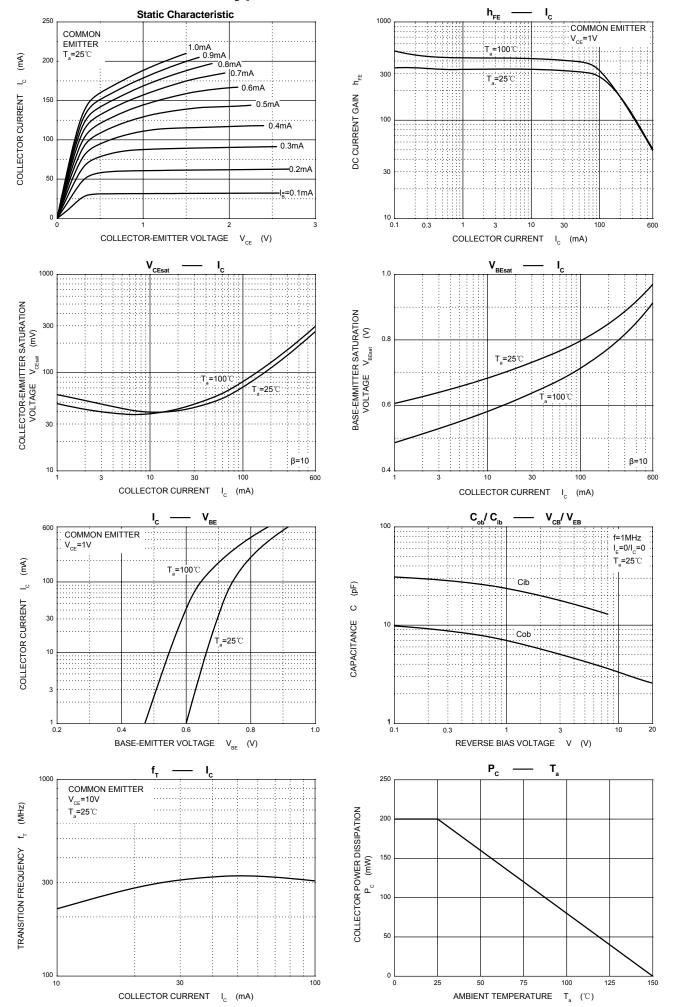
Parameter	Symbol	Test conditions		Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100 μA, I _E =0	60		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I _E = 100 μA, I _C =0	6		V
Collector cut-off current	I _{CBO}	V _{CB} = 50 V , I _E =0		0.1	μΑ
Collector cut-off current	I _{CEO}	V _{CE} = 35 V , I _B =0		0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5V , I _C =0		0.1	μΑ
	h _{FE(1)}	V _{CE} = 1V, I _C = 0.1mA	20		
	h _{FE(2)}	V _{CE} = 1V, I _C = 1mA	40		
DC current gain	h _{FE(3)}	V _{CE} = 1V, I _C = 10mA	80		
	h _{FE(4)}	V _{CE} = 1V, I _C = 150mA	100	300	
	h _{FE(5)}	V _{CE} = 2V, I _C = 500mA	40		
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =150 mA, I _B = 15mA		0.4	V
Collector-enlitter Saturation voltage	V _{CE(sat)2}	I _C =500 mA, I _B = 50mA		0.75	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C = 150 mA, I _B = 15mA	0.75	0.95	V
base-eiiiittei saturation voitage	V _{BE(sat)2}	I _C = 500 mA, I _B = 50mA		1.2	V
Transition frequency	f _T	V _{CE} = 10V,I _C = 20mA,f=100MHz	250		MHz
Output capacitance		V _{CB} =5V, I _E = 0,f=1MHz		6.5	pF
Delay time	t _d	V _{CC} =30V,		15	nS
Rise time	t _r	V _{BE} =2V,I _C =150mA ,I _{B1} =15mA		20	nS
Storage time	ts	V _{CC} =30V, I _C =150mA,I _{B1} =-I _{B2} =15mA		225	nS
Fall time	t _f			30	nS



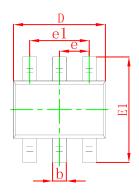
Typical Characteristics

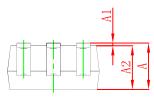


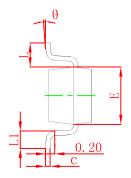




SOT-363 Package Outline Dimensions

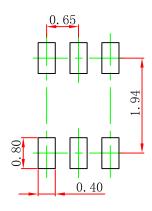






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650 TYP		0.026	3 TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

SOT-363 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	OTY
MMDT4401	SOT-363	3000



Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specificationsof any andall MSKSEMI Semiconductor products described orcontained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringementsof intellectual property rights or other rightsof third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

单击下面可查看定价,库存,交付和生命周期等信息

>>MSKSEMI (美森科)